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Autor: Colombo, L. / Borghesi, A. / Rojas, S.
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COMPARATIVE INFRARED VIBRATIONAL SPECTROSCOPY OF CHEMICAL VAPOUR DEPOSITION SiO₂ FILMS

L.Colombo^(a,b), A.Borghesi^(b), S.Rojas^(c) and Wing S.Wu^(c)

^(a) IRRMA, EPFL CH-1015 LAUSANNE, Switzerland

^(b) Dipartimento di Fisica "A.Volta", via Bassi 6, I-27100 PAVIA, Italy

^(c) SGS-Thomson Microelectronics, via Olivetti 2, I-20041 AGRATE BRIANZA (Mi), Italy

Abstract: We compare FTIR absorbance spectra due to Si-O stretching, Si-O-Si and O-Si-O bendings in different films of amorphous SiO₂. We study the effect of thermal annealing on these optical structures.

1. Introduction

Amorphous SiO₂ is a very important material in semiconductor devices manufacturing. Nevertheless, in spite of its fundamental importance as dielectric film, very few information about optical, dynamical and structural properties of SiO₂ is at present available. In the present work we apply Fourier transform infrared (FTIR) spectroscopy to the study of vibrational properties of Si-O, Si-O-Si and O-Si-O bonds as function of sample preparation: We compare the cases of thermal oxidation, chemical vapour deposition (CVD) from atmospheric pressure (APCVD) or from low-pressure (LPCVD) and plasma activated SiO₂ films [1].

2. Results and discussion

Accordingly to the structural description of SiO₂ [2], three different effective oscillators are identified in the FTIR spectra: They correspond to the Si-O bond stretching vibration and to the Si-O-Si and O-Si-O bond bending oscillations. The bond stretching and bending are described by a central two-body potential and by a three-body non central (Keating-like) potential, respectively. Following the current literature, we attribute to the Si-O stretching a frequency of 1050 cm⁻¹ and to Si-O-Si and O-Si-O bendings a frequency of 450 cm⁻¹ and 800 cm⁻¹, respectively. In Table I we summarize the peak parameters for as deposited and annealed films. F is the wave number peak position (in cm⁻¹); H is the peak height (in 10⁻³ absorbance units); FWHM is the full width half medium of the absorbance bands (in cm⁻¹). The main conclusions we may drawn are that after annealing the 1050 and 450 cm⁻¹ peaks are

shifted towards higher frequencies, while the O-Si-O peak is lowered in frequency; the FWHM is strongly reduced in any case and the absorption coefficient is always enhanced. In conclusion, the annealing can be regarded as an ordering process which causes a long-range disorder reduction (*i.e.* a recovering of the crystalline character of the sample); moreover, the statistical distribution of lattice parameters (Si-O bond length and Si-O-Si and O-Si-O bond angle) is also reduced and, consequently, FWHM decreases.

Table I

Film type	450 cm ⁻¹ peak			815 cm ⁻¹ peak			1080 cm ⁻¹ peak		
	<i>F</i>	<i>A</i>	FWHM	<i>F</i>	<i>A</i>	FWHM	<i>F</i>	<i>A</i>	FWHM
dry thermal oxide (1100 °C)	459.0	81	41	806.1	23	69	1080	230	77
APCVD (as deposited) (415 °C)	444.5	33	60	810.0	11	81	1059	128	87
APCVD (annealed) (415 °C)	458.0	60	44	812.0	10	63	1076	182	77
LPCVD (as deposited) (425 °C)	447.5	39	60	815.8	9	65	1057	131	87
LPCVD (annealed) (425 °C)	458.0	70	43	810.0	12	65	1078	206	75
PACVD (as deposited) (380 °C)	447.5	37	59	815.8	9	71	1053	130	93
PACVD (annealed) (380 °C)	458.0	64	43	812.0	11	57	1074	187	75

3. References

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